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# HM51W17800 Series

2,097,152-word × 8-bit Dynamic RAM

# HITACHI

ADE-203-664C (Z)

Rev. 3.0

Feb. 24, 1997

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## Description

The Hitachi HM51W17800 is a CMOS dynamic RAM organized 2,097,152-word × 8-bit. It employs the most advanced CMOS technology for high performance and low power. The HM51W17800 offers Fast Page Mode as a high speed access mode. Multiplexed address input permits the HM51W17800 to be packaged in standard 28-pin plastic SOJ and 28-pin TSOP.

## Features

- Single 3.3 V ( $\pm 0.3$  V)
- Access time: 50 ns/60 ns/70 ns (max)
- Power dissipation
  - Active mode: 396 mW/360 mW/324 mW (max)
  - Standby mode : 7.2 mW (max)  
: 0.54 mW (max) (L-version)
- Fast page mode capability
- Refresh cycles
  - 2048 refresh cycles : 32 ms  
: 128 ms (L-version)
- 4 variations of refresh
  - $\overline{\text{RAS}}$ -only refresh
  - $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$  refresh
  - Hidden refresh
  - Self refresh (L-version)
- Battery backup operation (L-version)

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## HM51W17800 Series

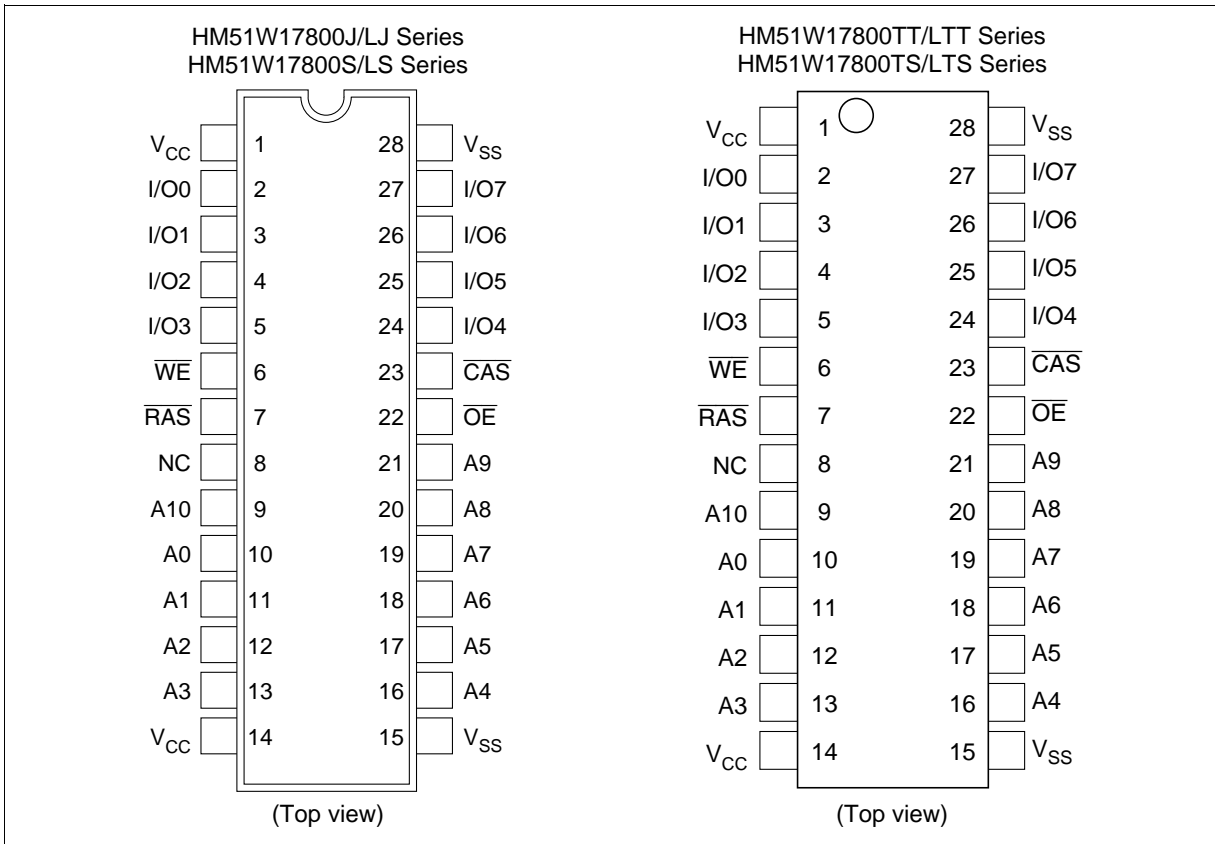
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### Ordering Information

Type No.	Access time	Package
HM51W17800J-5	50 ns	400-mil 28-pin plastic SOJ (CP-28DA)
HM51W17800J-6	60 ns	
HM51W17800J-7	70 ns	
HM51W17800LJ-5	50 ns	
HM51W17800LJ-6	60 ns	
HM51W17800LJ-7	70 ns	
HM51W17800S-5	50 ns	300-mil 28-pin plastic SOJ (CP-28DNA)
HM51W17800S-6	60 ns	
HM51W17800S-7	70 ns	
HM51W17800LS-5	50 ns	
HM51W17800LS-6	60 ns	
HM51W17800LS-7	70 ns	
HM51W17800TT-5	50 ns	400-mil 28-pin plastic TSOP II (TTP-28DA)
HM51W17800TT-6	60 ns	
HM51W17800TT-7	70 ns	
HM51W17800LTT-5	50 ns	
HM51W17800LTT-6	60 ns	
HM51W17800LTT-7	70 ns	
HM51W17800TS-5	50 ns	300-mil 28-pin plastic TSOP II (TTP-28DB)
HM51W17800TS-6	60 ns	
HM51W17800TS-7	70 ns	
HM51W17800LTS-5	50 ns	
HM51W17800LTS-6	60 ns	
HM51W17800LTS-7	70 ns	

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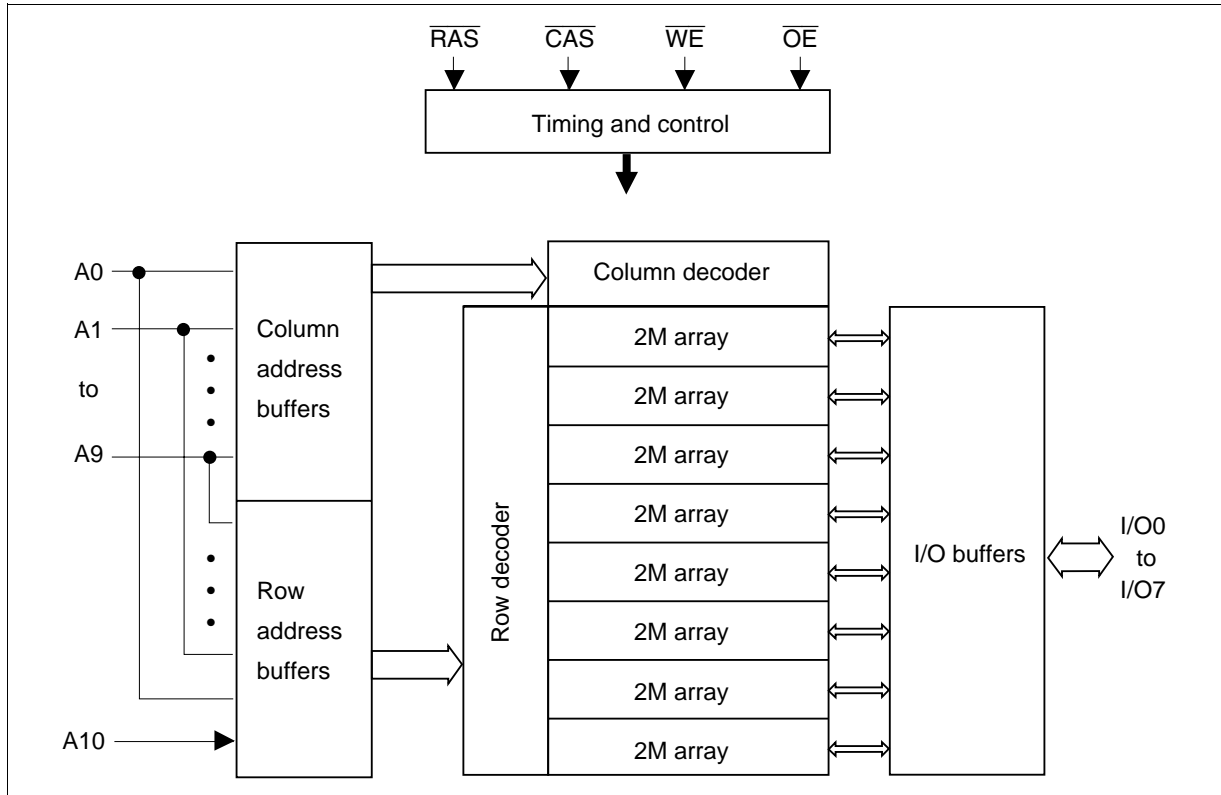
## Pin Arrangement



## Pin Description

Pin name	Function
A0 to A10	Address input — Row/Refresh address A0 to A10 — Column address A0 to A9
I/O0 to I/O7	Data input/data output
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{WE}}$	Read/Write enable
$\overline{\text{OE}}$	Output enable
$V_{\text{CC}}$	Power supply
$V_{\text{SS}}$	Ground
NC	No connection

## Block Diagram



**Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Voltage on any pin relative to $V_{SS}$	$V_T$	-0.5 to + 4.6	V
Supply voltage relative to $V_{SS}$	$V_{CC}$	-0.5 to + 4.6	V
Short circuit output current	$I_{out}$	50	mA
Power dissipation	$P_T$	1.0	W
Operating temperature	$T_{opr}$	0 to +70	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

**Recommended DC Operating Conditions ( $T_a = 0$  to +70°C)**

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply voltage	$V_{CC}$	3.0	3.3	3.6	V	1, 2
Input high voltage	$V_{IH}$	2.0	—	$V_{CC} + 0.3$	V	1
Input low voltage	$V_{IL}$	-0.3	—	0.8	V	1

Notes: 1. All voltage referred to  $V_{SS}$

# HM51W17800 Series

DC Characteristics ( $T_a = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ ,  $V_{SS} = 0 \text{ V}$ )

Parameter	Symbol	HM51W17800						Unit	Test conditions
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
Operating current* <sup>1</sup> , * <sup>2</sup>	$I_{CC1}$	—	110	—	100	—	90	mA	$t_{RC} = \text{min}$
Standby current	$I_{CC2}$	—	2	—	2	—	2	mA	TTL interface $\overline{\text{RAS}}, \overline{\text{CAS}} = V_{IH}$ Dout = High-Z
		—	1	—	1	—	1	mA	CMOS interface $\overline{\text{RAS}}, \overline{\text{CAS}} \geq V_{CC} - 0.2\text{V}$ Dout = High-Z
Standby current (L-version)	$I_{CC2}$	—	150	—	150	—	150	$\mu\text{A}$	CMOS interface $\overline{\text{RAS}}, \overline{\text{CAS}} \geq V_{CC} - 0.2\text{V}$ Dout = High-Z
$\overline{\text{RAS}}$ -only refresh current* <sup>2</sup>	$I_{CC3}$	—	110	—	100	—	90	mA	$t_{RC} = \text{min}$
Standby current* <sup>1</sup>	$I_{CC5}$	—	5	—	5	—	5	mA	$\overline{\text{RAS}} = V_{IH}$ $\overline{\text{CAS}} = V_{IL}$ Dout = enable
$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh current	$I_{CC6}$	—	110	—	100	—	90	mA	$t_{RC} = \text{min}$
Fast page mode current* <sup>1</sup> , * <sup>3</sup>	$I_{CC7}$	—	100	—	90	—	85	mA	$t_{PC} = \text{min}$
Battery backup current* <sup>4</sup> (Standby with CBR refresh) (L-version)	$I_{CC10}$	—	400	—	400	—	400	$\mu\text{A}$	CMOS interface Dout = High-Z CBR refresh: $t_{RC} = 62.5 \mu\text{s}$ $t_{RAS} \leq 0.3 \mu\text{s}$
Self refresh mode current (L-version)	$I_{CC11}$	—	250	—	250	—	250	$\mu\text{A}$	CMOS interface $\overline{\text{RAS}}, \overline{\text{CAS}} \leq 0.2\text{V}$ Dout = High-Z
Input leakage current	$I_{LI}$	-10	10	-10	10	-10	10	$\mu\text{A}$	$0 \text{ V} \leq V_{in} \leq 4.6 \text{ V}$
Output leakage current	$I_{LO}$	-10	10	-10	10	-10	10	$\mu\text{A}$	$0 \text{ V} \leq V_{out} \leq 4.6 \text{ V}$ Dout = disable
Output high voltage	$V_{OH}$	2.4	$V_{CC}$	2.4	$V_{CC}$	2.4	$V_{CC}$	V	High Iout = -2 mA
Output low voltage	$V_{OL}$	0	0.4	0	0.4	0	0.4	V	Low Iout = 2 mA

Notes: 1.  $I_{CC}$  depends on output load condition when the device is selected.  $I_{CC}$  max is specified at the output open condition.

2. Address can be changed once or less while  $\overline{\text{RAS}} = V_{IL}$ .

3. Address can be changed once or less while  $\overline{\text{CAS}} = V_{IH}$ .

4.  $\overline{\text{CAS}} = L (\leq 0.2 \text{ V})$  while  $\overline{\text{RAS}} = L (\leq 0.2 \text{ V})$ .

**Capacitance** ( $T_a = 25^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$ )

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	$C_{I1}$	—	5	pF	1
Input capacitance (Clocks)	$C_{I2}$	—	7	pF	1
Output capacitance (Data-in, Data-out)	$C_{I/O}$	—	7	pF	1, 2

Notes: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.  
 2.  $\overline{\text{CAS}} = V_{IH}$  to disable Dout.

**AC Characteristics** ( $T_a = 0$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$ ,  $V_{SS} = 0\text{ V}$ )<sup>\*1, \*2, \*18</sup>
**Test Conditions**

- Input rise and fall time: 5 ns
- Input timing reference levels: 0.8 V, 2.0 V
- Output timing reference levels: 0.8 V, 2.0 V
- Output load: 1 TTL gate +  $C_L$  (100 pF) (Including scope and jig)

# HM51W17800 Series

## Read, Write, Read-Modify-Write and Refresh Cycles (Common parameters)

Parameter	Symbol	HM51W17800						Unit	Notes
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
Random read or write cycle time	$t_{RC}$	90	—	110	—	130	—	ns	
$\overline{RAS}$ precharge time	$t_{RP}$	30	—	40	—	50	—	ns	
$\overline{CAS}$ precharge time	$t_{CP}$	8	—	10	—	10	—	ns	
$\overline{RAS}$ pulse width	$t_{RAS}$	50	10000	60	10000	70	10000	ns	
$\overline{CAS}$ pulse width	$t_{CAS}$	13	10000	15	10000	18	10000	ns	
Row address setup time	$t_{ASR}$	0	—	0	—	0	—	ns	
Row address hold time	$t_{RAH}$	8	—	10	—	10	—	ns	
Column address setup time	$t_{ASC}$	0	—	0	—	0	—	ns	
Column address hold time	$t_{CAH}$	8	—	10	—	15	—	ns	
$\overline{RAS}$ to $\overline{CAS}$ delay time	$t_{RCD}$	18	37	20	45	20	52	ns	3
$\overline{RAS}$ to column address delay time	$t_{RAD}$	13	25	15	30	15	35	ns	4
$\overline{RAS}$ hold time	$t_{RSH}$	13	—	15	—	18	—	ns	
$\overline{CAS}$ hold time	$t_{CSH}$	50	—	60	—	70	—	ns	
$\overline{CAS}$ to $\overline{RAS}$ precharge time	$t_{CRP}$	5	—	5	—	5	—	ns	
$\overline{OE}$ to Din delay time	$t_{OED}$	13	—	15	—	18	—	ns	5
$\overline{OE}$ delay time from Din	$t_{DZO}$	0	—	0	—	0	—	ns	6
$\overline{CAS}$ delay time from Din	$t_{DZC}$	0	—	0	—	0	—	ns	6
Transition time (rise and fall)	$t_T$	3	50	3	50	3	50	ns	7



Read Cycle

Parameter	Symbol	HM51W17800						Unit	Notes
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
Access time from $\overline{\text{RAS}}$	$t_{\text{RAC}}$	—	50	—	60	—	70	ns	8, 9
Access time from $\overline{\text{CAS}}$	$t_{\text{CAC}}$	—	13	—	15	—	18	ns	9, 10, 17,
Access time from address	$t_{\text{AA}}$	—	25	—	30	—	35	ns	9, 11, 17,
Access time from $\overline{\text{OE}}$	$t_{\text{OEA}}$	—	13	—	15	—	18	ns	9
Read command setup time	$t_{\text{RCS}}$	0	—	0	—	0	—	ns	
Read command hold time to $\overline{\text{CAS}}$	$t_{\text{RCH}}$	0	—	0	—	0	—	ns	12
Read command hold time to $\overline{\text{RAS}}$	$t_{\text{RRH}}$	0	—	0	—	0	—	ns	12
Column address to $\overline{\text{RAS}}$ lead time	$t_{\text{RAL}}$	25	—	30	—	35	—	ns	
Column address to $\overline{\text{CAS}}$ lead time	$t_{\text{CAL}}$	25	—	30	—	35	—	ns	
$\overline{\text{CAS}}$ to output in low-Z	$t_{\text{CLZ}}$	0	—	0	—	0	—	ns	
Output data hold time	$t_{\text{OH}}$	3	—	3	—	3	—	ns	
Output data hold time from $\overline{\text{OE}}$	$t_{\text{OHO}}$	3	—	3	—	3	—	ns	
Output buffer turn-off time	$t_{\text{OFF}}$	—	13	—	15	—	15	ns	13
Output buffer turn-off to $\overline{\text{OE}}$	$t_{\text{OEZ}}$	—	13	—	15	—	15	ns	13
$\overline{\text{CAS}}$ to Din delay time	$t_{\text{CDD}}$	13	—	15	—	18	—	ns	5

Write Cycle

Parameter	Symbol	HM51W17800						Unit	Notes
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
Write command setup time	$t_{\text{WCS}}$	0	—	0	—	0	—	ns	14
Write command hold time	$t_{\text{WCH}}$	8	—	10	—	15	—	ns	
Write command pulse width	$t_{\text{WP}}$	8	—	10	—	10	—	ns	
Write command to $\overline{\text{RAS}}$ lead time	$t_{\text{RWL}}$	13	—	15	—	18	—	ns	
Write command to $\overline{\text{CAS}}$ lead time	$t_{\text{CWL}}$	13	—	15	—	18	—	ns	
Data-in setup time	$t_{\text{DS}}$	0	—	0	—	0	—	ns	15
Data-in hold time	$t_{\text{DH}}$	8	—	10	—	15	—	ns	15

# HM51W17800 Series

## Read-Modify-Write Cycle

Parameter	Symbol	HM51W17800						Unit	Notes
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
Read-modify-write cycle time	$t_{RWC}$	131	—	155	—	181	—	ns	
$\overline{RAS}$ to $\overline{WE}$ delay time	$t_{RWD}$	73	—	85	—	98	—	ns	14
$\overline{CAS}$ to $\overline{WE}$ delay time	$t_{CWD}$	36	—	40	—	46	—	ns	14
Column address to $\overline{WE}$ delay time	$t_{AWD}$	48	—	55	—	63	—	ns	14
$\overline{OE}$ hold time from $\overline{WE}$	$t_{OEH}$	13	—	15	—	18	—	ns	

## Refresh Cycle

Parameter	Symbol	HM51W17800						Unit	Notes
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
$\overline{CAS}$ setup time (CBR refresh cycle)	$t_{CSR}$	5	—	5	—	5	—	ns	
$\overline{CAS}$ hold time (CBR refresh cycle)	$t_{CHR}$	8	—	10	—	10	—	ns	
$\overline{WE}$ setup time (CBR refresh cycle)	$t_{WRP}$	0	—	0	—	0	—	ns	
$\overline{WE}$ hold time (CBR refresh cycle)	$t_{WRH}$	8	—	10	—	10	—	ns	
$\overline{RAS}$ precharge to $\overline{CAS}$ hold time	$t_{RPC}$	5	—	5	—	5	—	ns	

## Fast Page Mode Cycle

Parameter	Symbol	HM51W17800						Unit	Notes
		-5		-6		-7			
		Min	Max	Min	Max	Min	Max		
Fast page mode cycle time	$t_{PC}$	35	—	40	—	45	—	ns	
Fast page mode $\overline{RAS}$ pulse width	$t_{RASP}$	—	100000	—	100000	—	100000	ns	16
Access time from $\overline{CAS}$ precharge	$t_{CPA}$	—	30	—	35	—	40	ns	9, 17
$\overline{RAS}$ hold time from $\overline{CAS}$ precharge	$t_{CPRH}$	30	—	35	—	40	—	ns	

Fast Page Mode Read-Modify-Write Cycle

		HM51W17800							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Fast page mode read-modify-write cycle time	$t_{PRWC}$	76	—	85	—	96	—	ns	
$\overline{WE}$ delay time from $\overline{CAS}$ precharge	$t_{CPW}$	53	—	60	—	68	—	ns	14

Refresh

Parameter	Symbol	Max	Unit	Note
Refresh period	$t_{REF}$	32	ms	2048 cycles
Refresh period (L-version)	$t_{REF}$	128	ms	2048 cycles

Self Refresh Mode (L-version)

		HM51W17800L							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
$\overline{RAS}$ pulse width (self refresh)	$t_{RASS}$	100	—	100	—	100	—	$\mu$ s	19, 20, 21, 22
$\overline{RAS}$ precharge time (self refresh)	$t_{RPS}$	90	—	110	—	130	—	ns	
$\overline{CAS}$ hold time (self refresh)	$t_{CHS}$	-50	—	-50	—	-50	—	ns	

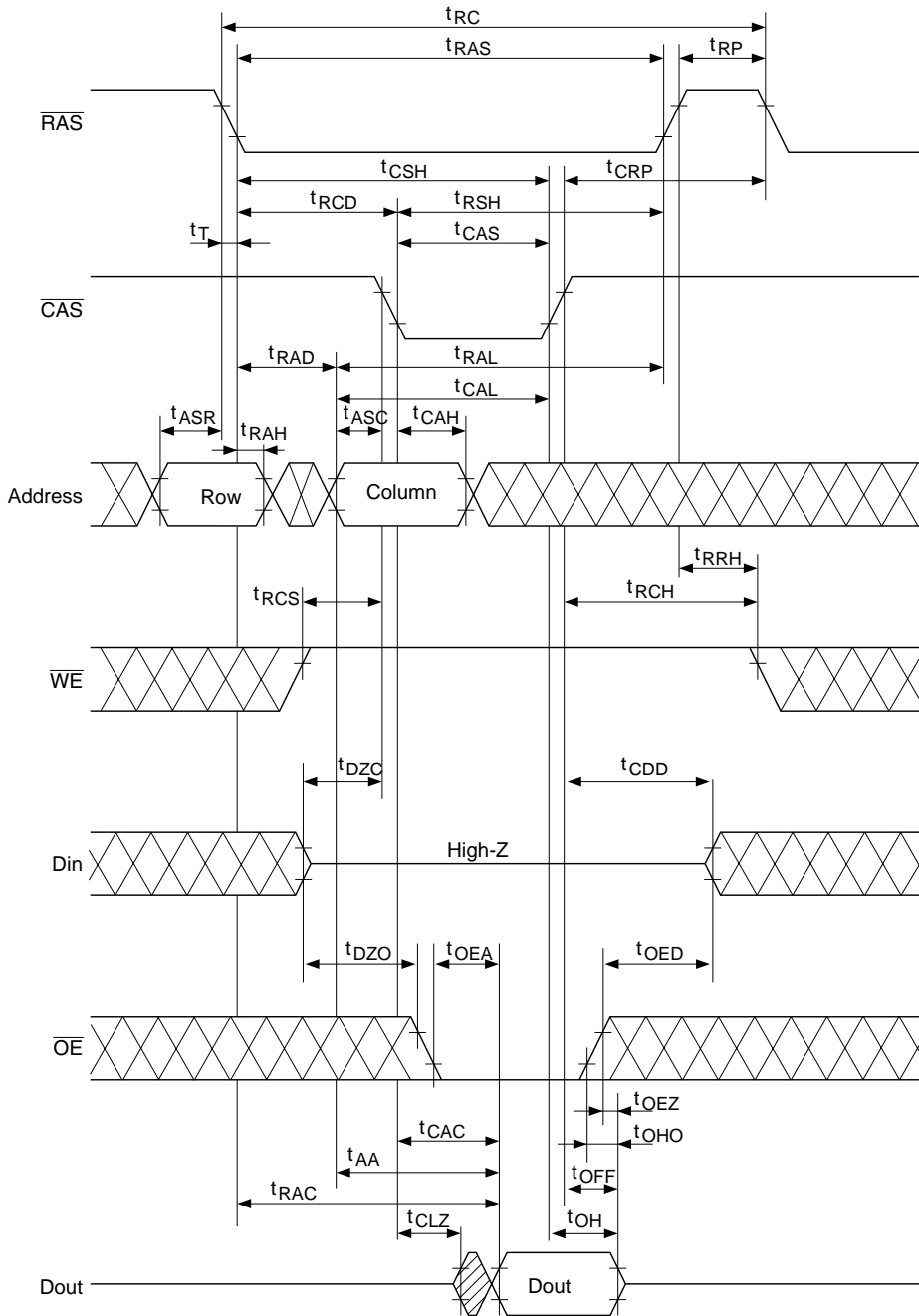
Notes: 1. AC measurements assume  $t_T = 5$  ns.

- An initial pause of 200  $\mu$ s is required after power up followed by a minimum of eight initialization cycles (any combination of cycles containing  $\overline{RAS}$ -only refresh or  $\overline{CAS}$ -before- $\overline{RAS}$  refresh). If the internal refresh counter is used, a minimum of eight  $\overline{CAS}$ -before- $\overline{RAS}$  refresh cycles are required.
- Operation with the  $t_{RCD}$  (max) limit insures that  $t_{RAC}$  (max) can be met,  $t_{RCD}$  (max) is specified as a reference point only; if  $t_{RCD}$  is greater than the specified  $t_{RCD}$  (max) limit, then access time is controlled exclusively by  $t_{CAC}$ .
- Operation with the  $t_{RAD}$  (max) limit insures that  $t_{RAC}$  (max) can be met,  $t_{RAD}$  (max) is specified as a reference point only; if  $t_{RAD}$  is greater than the specified  $t_{RAD}$  (max) limit, then access time is controlled exclusively by  $t_{AA}$ .
- Either  $t_{OED}$  or  $t_{CDD}$  must be satisfied.
- Either  $t_{DZO}$  or  $t_{DZC}$  must be satisfied.
- $V_{IH}$  (min) and  $V_{IL}$  (max) are reference levels for measuring timing of input signals. Also, transition times are measured between  $V_{IH}$  (min) and  $V_{IL}$  (max).
- Assumes that  $t_{RCD} \leq t_{RCD}$  (max) and  $t_{RAD} \leq t_{RAD}$  (max). If  $t_{RCD}$  or  $t_{RAD}$  is greater than the maximum recommended value shown in this table,  $t_{RAC}$  exceeds the value shown.
- Measured with a load circuit equivalent to 1 TTL loads and 100 pF. ( $V_{OH} = 2.0$  V,  $V_{OL} = 0.8$  V)
- Assumes that  $t_{RCD} \geq t_{RCD}$  (max) and  $t_{RAD} \leq t_{RAD}$  (max).
- Assumes that  $t_{RCD} \leq t_{RCD}$  (max) and  $t_{RAD} \geq t_{RAD}$  (max).

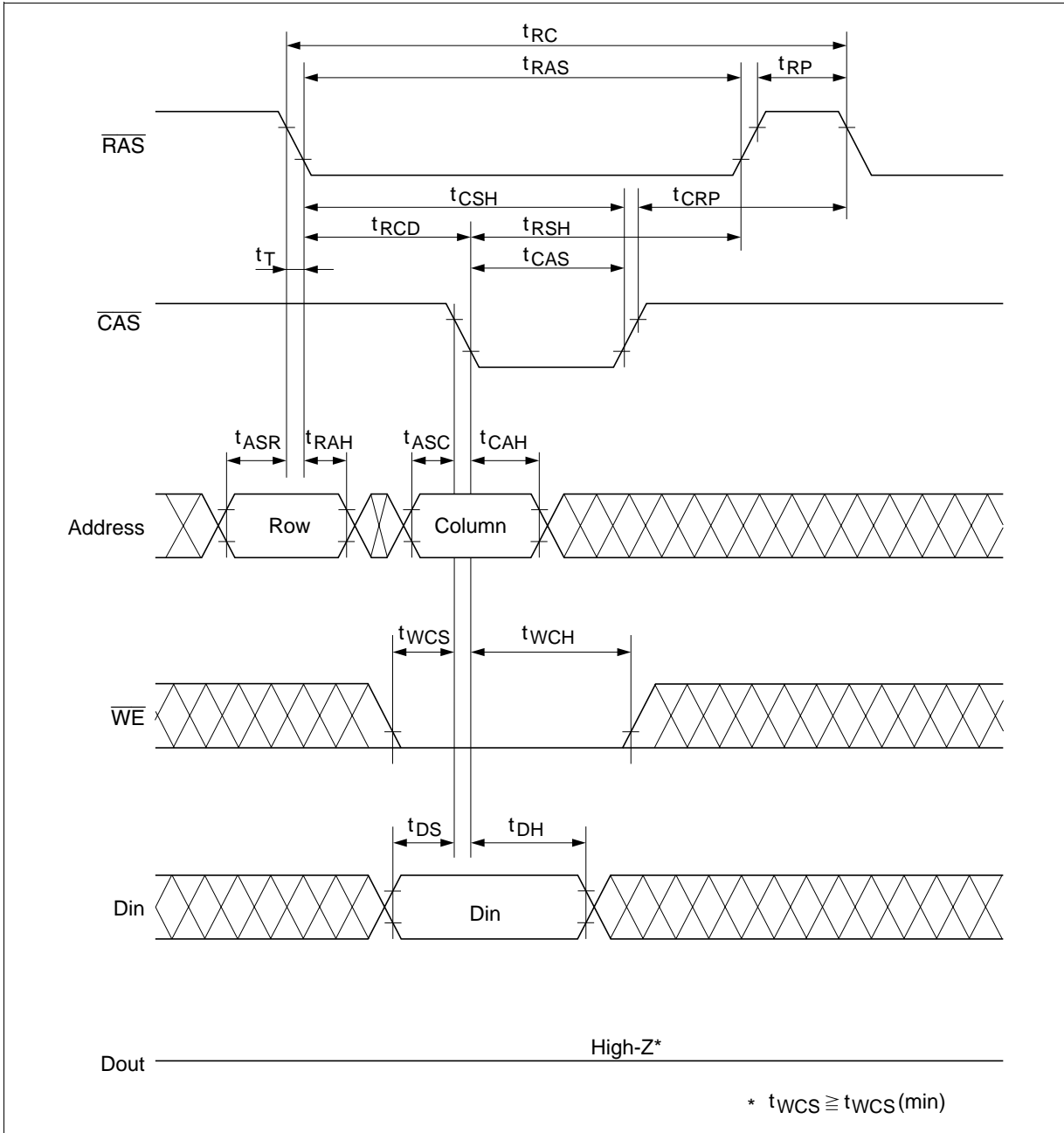
12. Either  $t_{RCH}$  or  $t_{RRH}$  must be satisfied for a read cycles.
13.  $t_{OFF}$  (max) and  $t_{OEZ}$  (max) define the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.
14.  $t_{WCS}$ ,  $t_{RWD}$ ,  $t_{CWD}$ ,  $t_{AWD}$  and  $t_{CPW}$  are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if  $t_{WCS} \geq t_{WCS}(\text{min})$ , the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if  $t_{RWD} \geq t_{RWD}(\text{min})$ ,  $t_{CWD} \geq t_{CWD}(\text{min})$ , and  $t_{AWD} \geq t_{AWD}(\text{min})$ , or  $t_{CWD} \geq t_{CWD}(\text{min})$ ,  $t_{AWD} \geq t_{AWD}(\text{min})$  and  $t_{CPW} \geq t_{CPW}(\text{min})$ , the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
15. These parameters are referred to  $\overline{CAS}$  leading edge in early write cycles and to  $\overline{WE}$  leading edge in delayed write or read-modify-write cycles.
16.  $t_{RASP}$  defines  $\overline{RAS}$  pulse width in Fast page mode cycles.
17. Access time is determined by the longest among  $t_{AA}$ ,  $t_{CAC}$  and  $t_{CPA}$ .
18. In delayed write or read-modify-write cycles,  $\overline{OE}$  must disable output buffer prior to applying data to the device.
19. Please do not use  $t_{RASS}$  timing,  $10 \mu\text{s} \leq t_{RASS} \leq 100 \mu\text{s}$ . During this period, the device is in transition state from normal operation mode to self refresh mode. If  $t_{RASS} \geq 100 \mu\text{s}$ , then  $\overline{RAS}$  precharge time should use  $t_{RPS}$  instead of  $t_{RP}$ .
20. If you use  $\overline{RAS}$  only refresh or CBR burst refresh mode in normal read/write cycles, 2048 cycles of distributed CBR refresh with  $15.6 \mu\text{s}$  interval should be executed within 32 ms immediately after exiting from and before entering into the self refresh mode.
21. If you use distributed CBR refresh mode with  $15.6 \mu\text{s}$  interval in normal read/write cycle, CBR refresh should be executed within  $15.6 \mu\text{s}$  immediately after exiting from and before entering into self refresh mode.
22. Repetitive self refresh mode without refreshing all memory is not allowed. Once you exit from self refresh mode, all memory cells need to be refreshed before re-entering the self refresh mode again.
23. XXX: H or L ( $H: V_{IH}(\text{min}) \leq V_{IN} \leq V_{IH}(\text{max})$ ,  $L: V_{IL}(\text{min}) \leq V_{IN} \leq V_{IL}(\text{max})$ )  
/////: Invalid Dout  
When the address, clock and input pins are not described on timing waveforms, their pins must be applied  $V_{IH}$  or  $V_{IL}$ .

Timing Waveforms\*23

Read Cycle



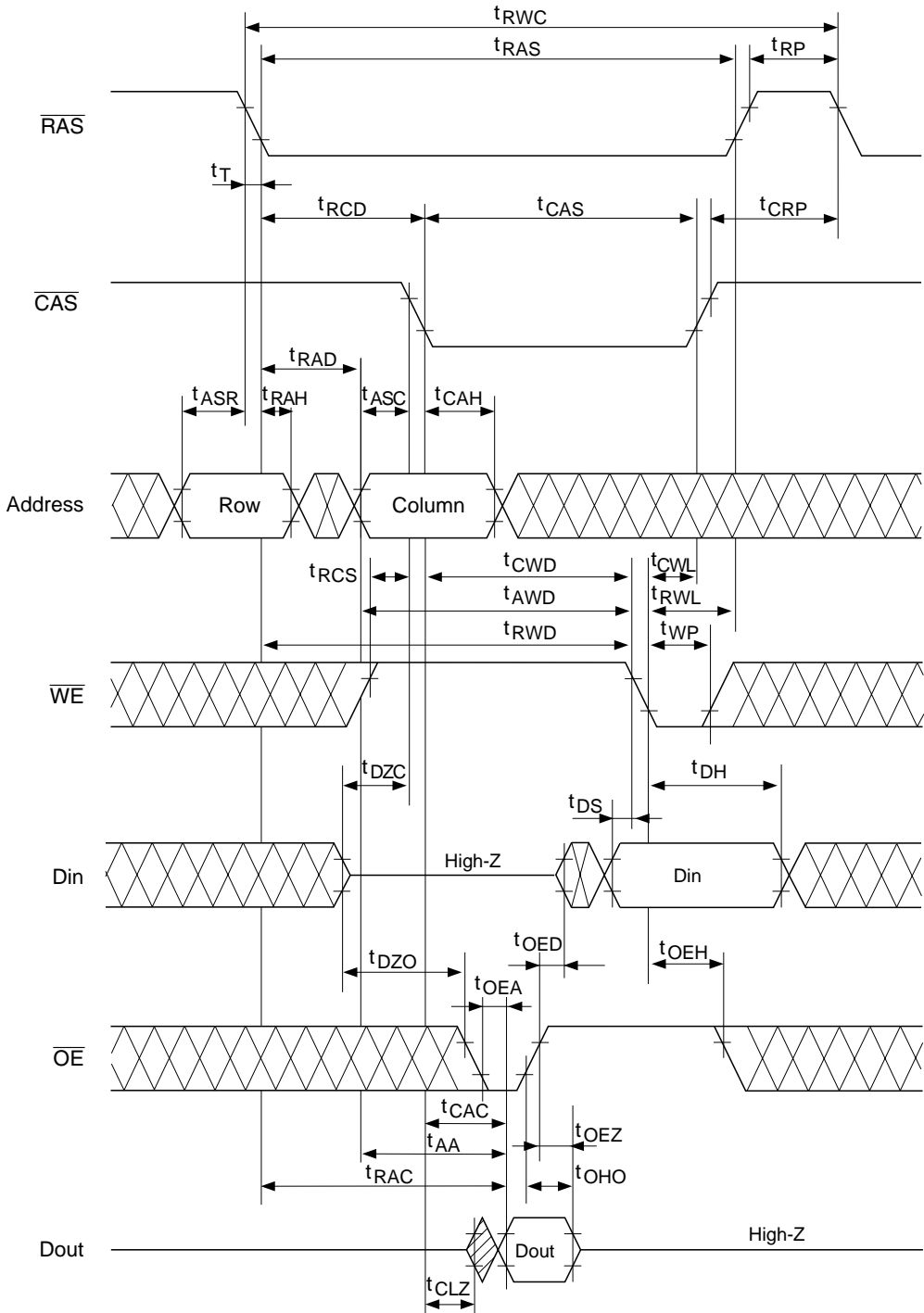
## Early Write Cycle





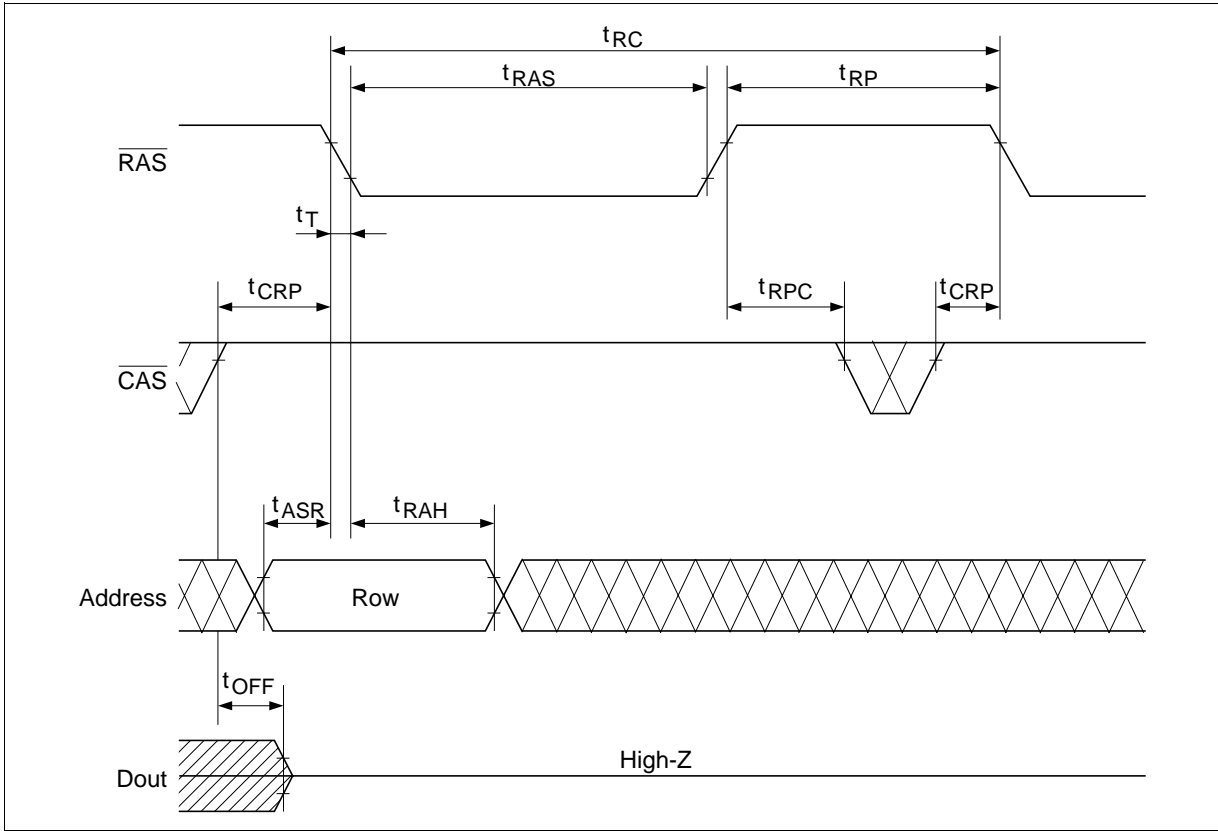
# HM51W17800 Series

## Read-Modify-Write Cycle\*18



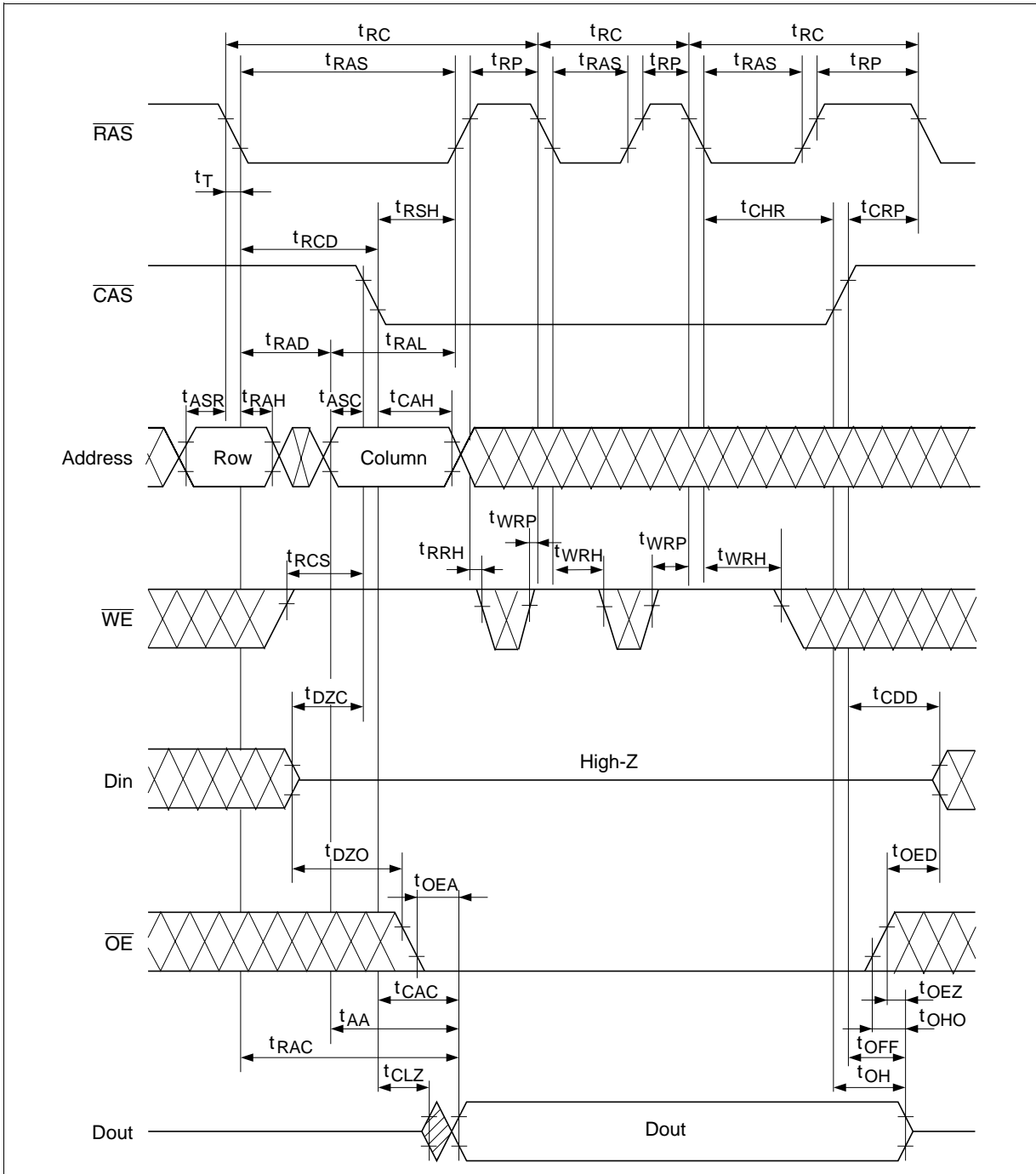


RAS-Only Refresh Cycle

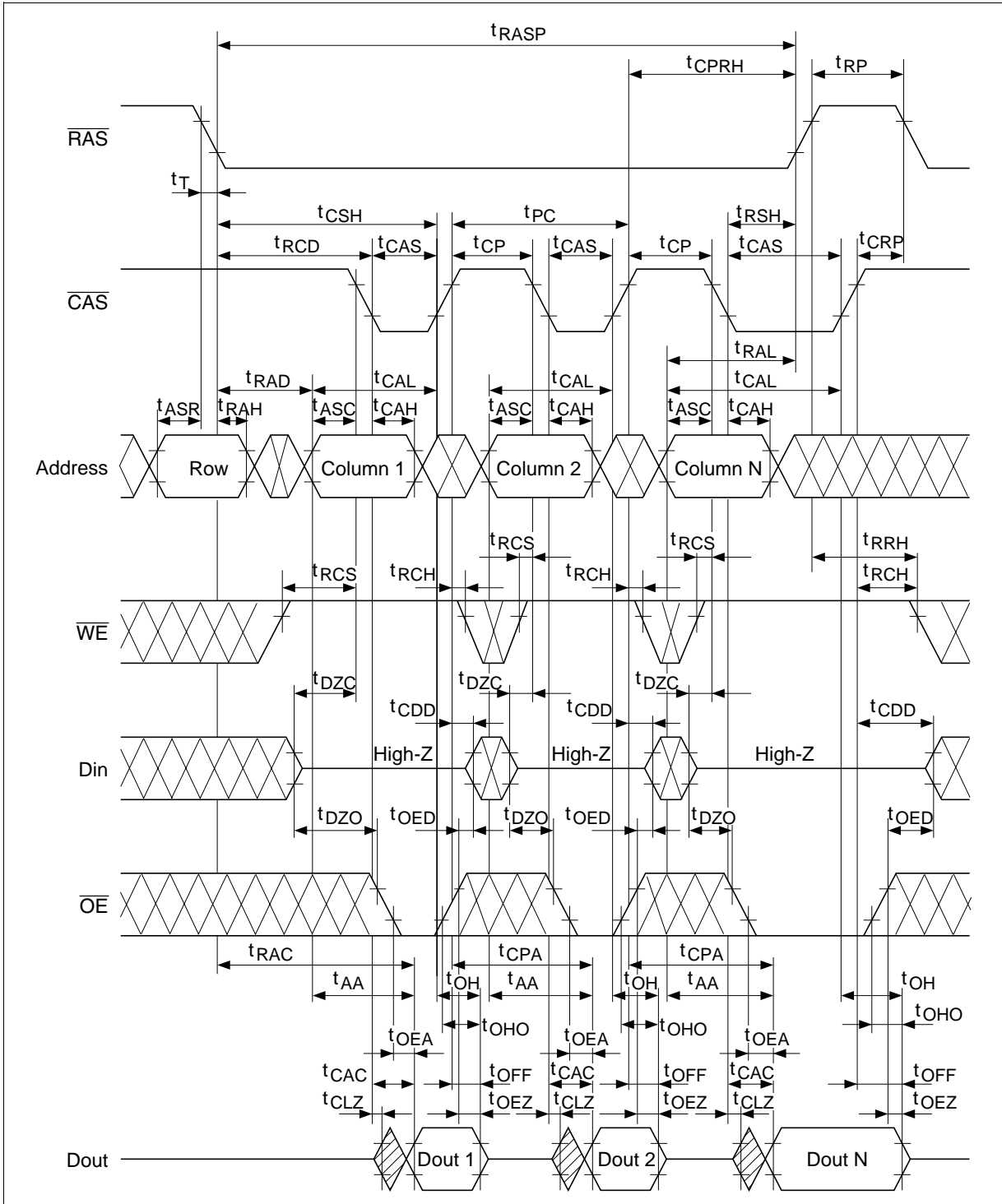




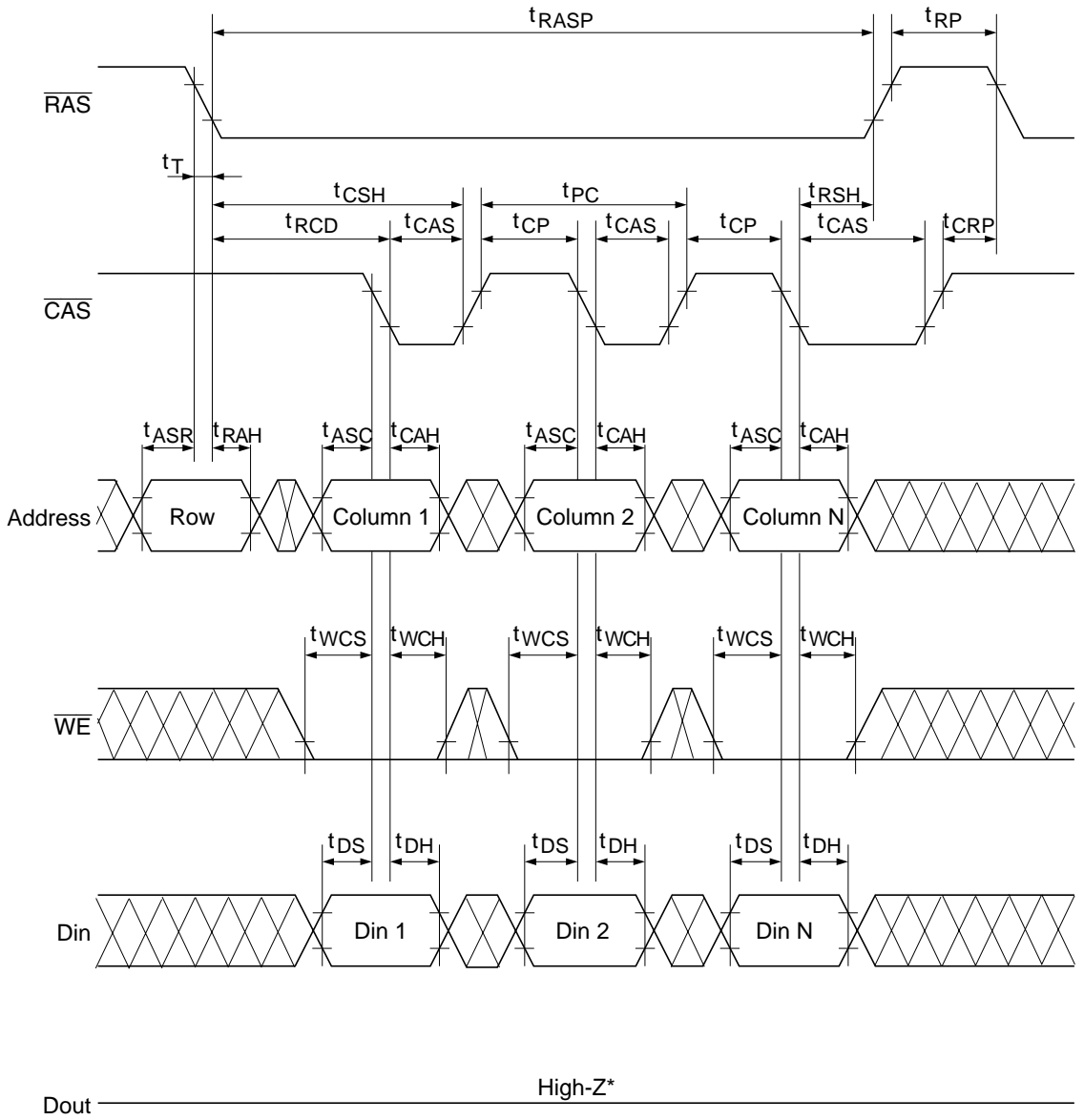
Hidden Refresh Cycle



## Fast Page Mode Read Cycle



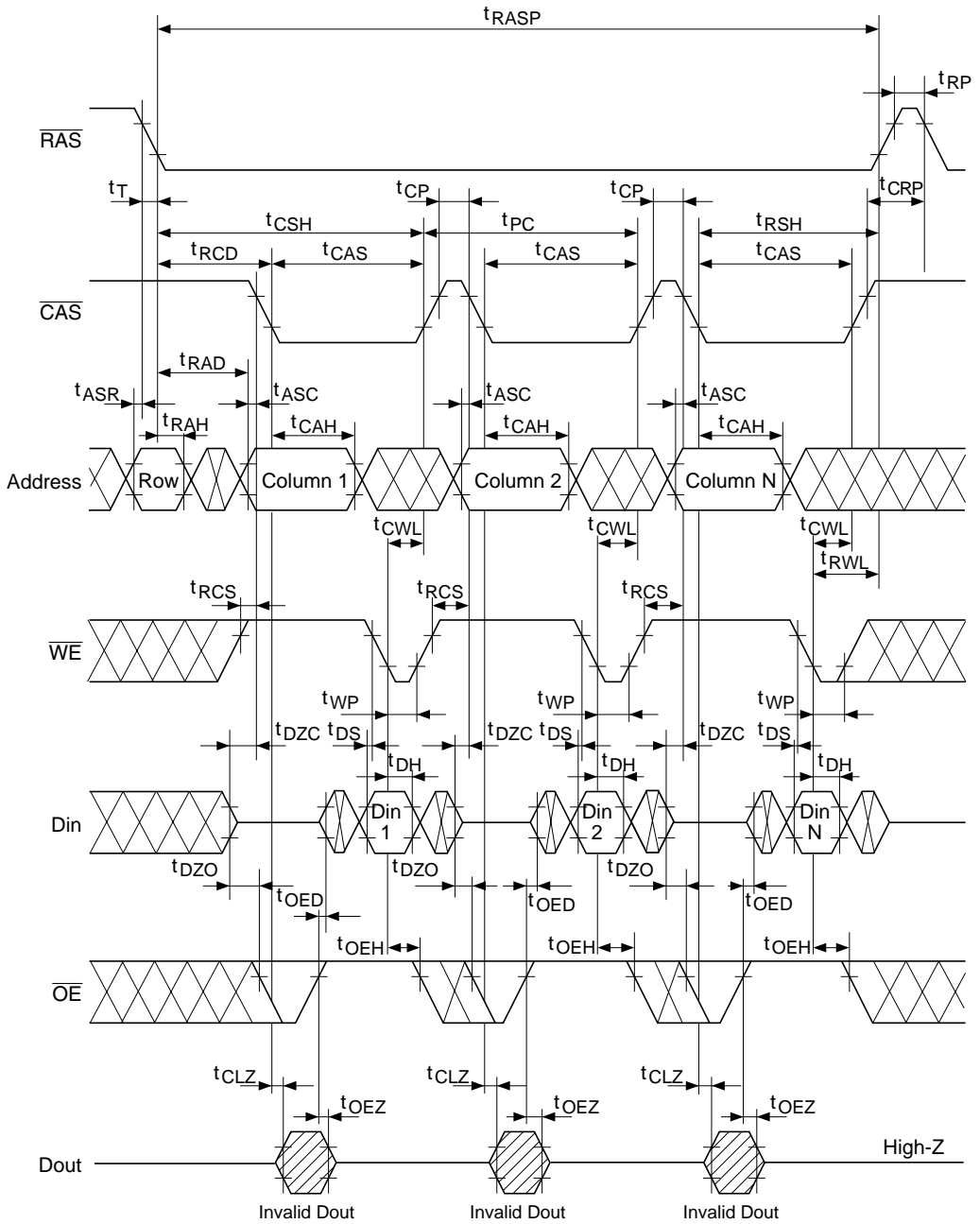
Fast Page Mode Early Write Cycle



\*  $t_{WCS} \geq t_{WCS}(\text{min})$

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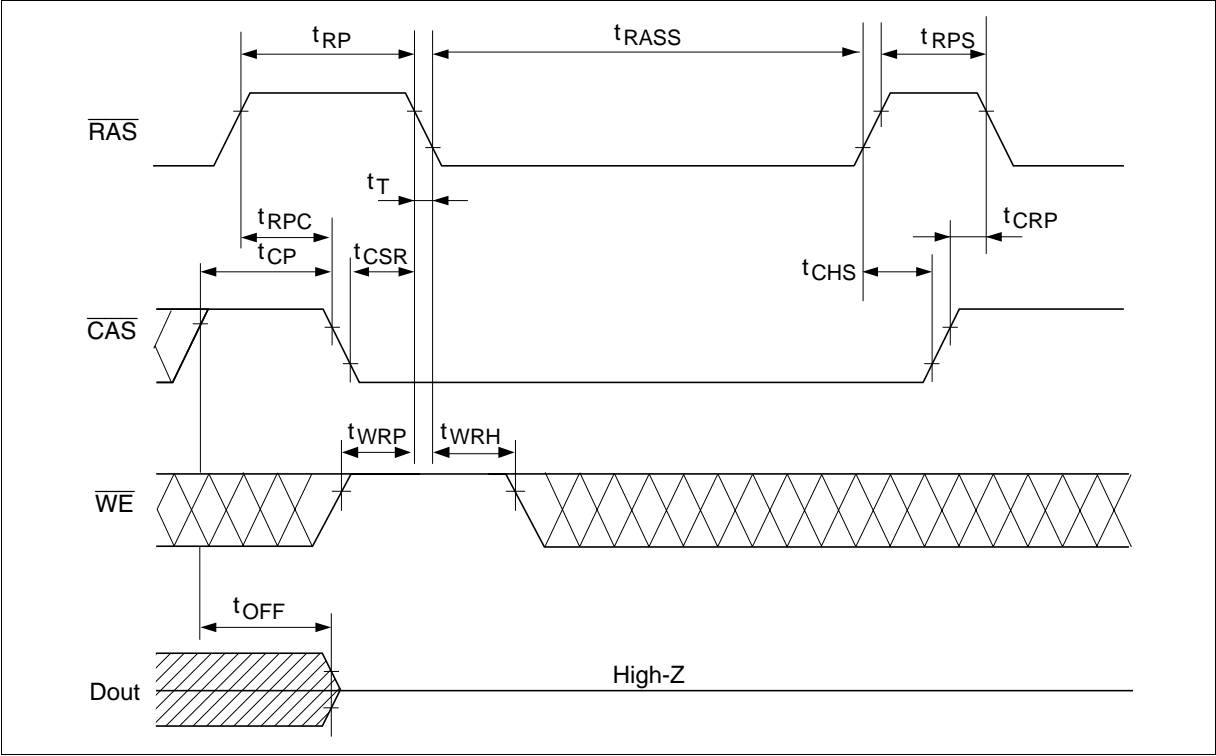
## Fast Page Mode Delayed Write Cycle\*18





# HM51W17800 Series

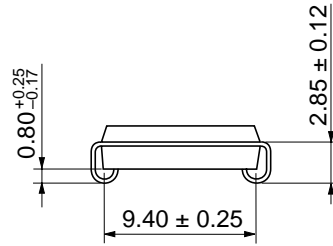
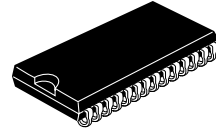
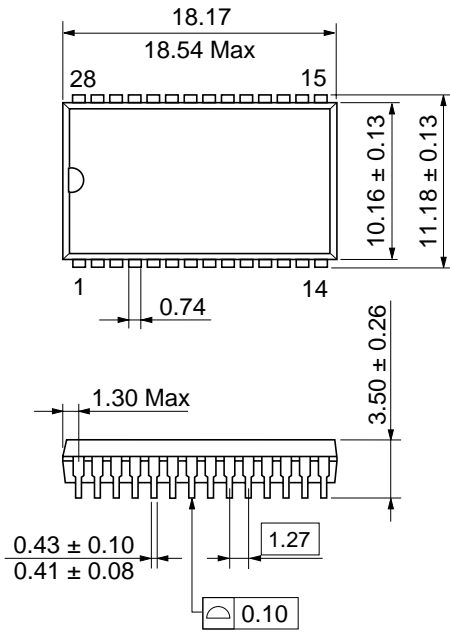
## Self Refresh Cycle (L-version)\*19, \*20, \*21, \*22





Package Dimensions

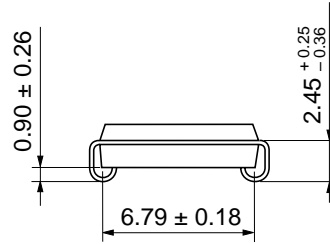
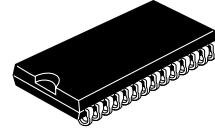
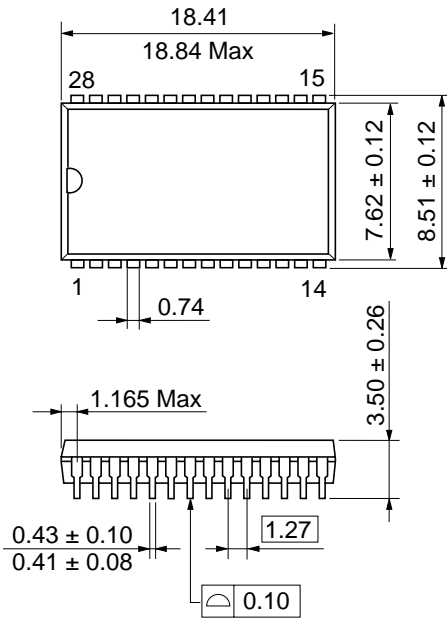
HM51W17800J/LJ Series (CP-28DA)



Hitachi Code	CP-28DA
JEDEC Code	MO-061-AA
EIAJ Code	SC-637-B
Weight	1.16 g

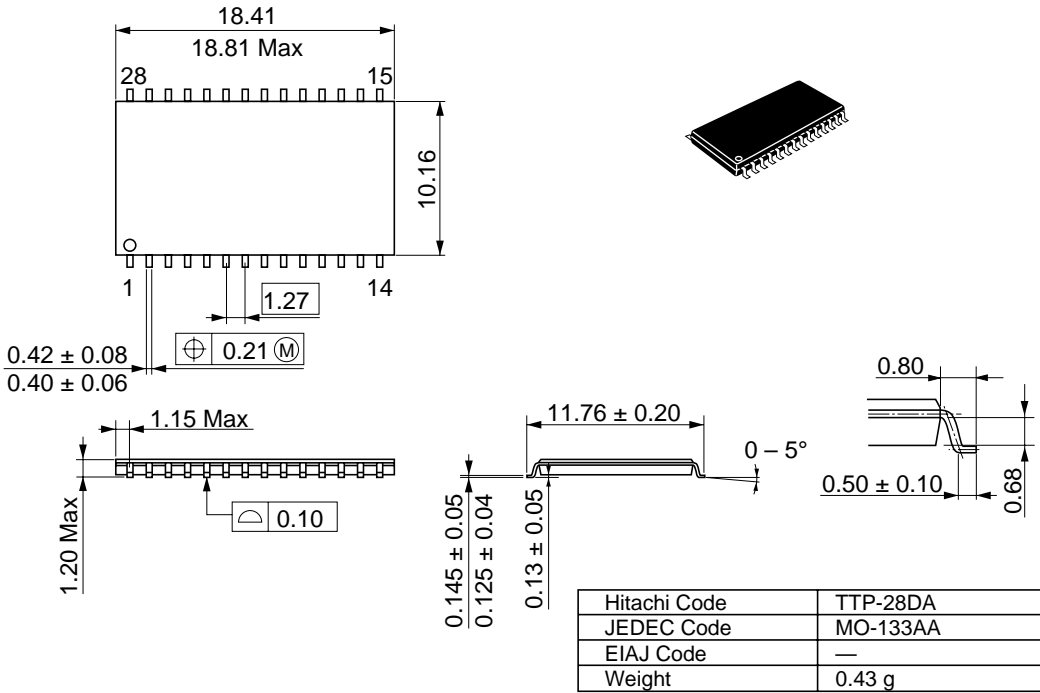
# HM51W17800 Series

## HM51W17800S/LS Series (CP-28DNA)



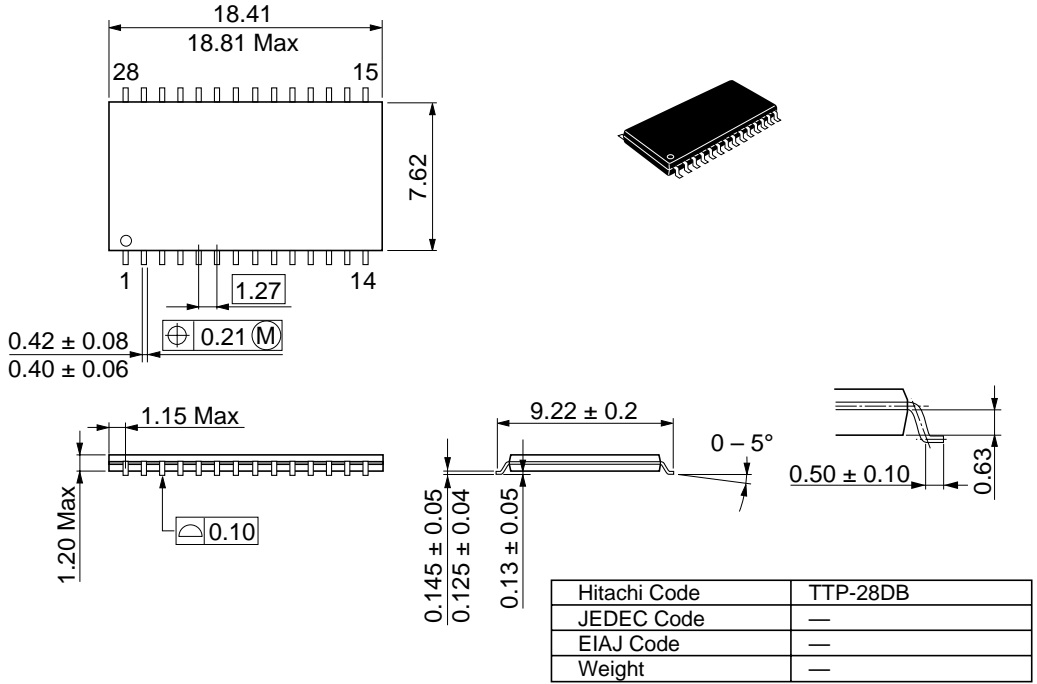
Hitachi Code	CP-28DNA
JEDEC Code	—
EIAJ Code	—
Weight	—

HM51W17800TT/LTT Series (TTP-28DA)



# HM51W17800 Series

## HM51W17800TS/LTS Series (TTP-28DB)



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# HM51W17800 Series

## Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
1.0	Sep. 30, 1996	Initial issue	Y. Kasama	M. Mishima
2.0	Dec. 5, 1996	Addition of HM51W17800-5 Series Addition of HM51W17800S/LS Series (CP-28DNA) Addition of HM51W17800TS/LTS Series (TTP-28DB) Power dissipation (active) 432/396 mW(max) to 396/360/324 mW (max) DC Characteristics I <sub>CC1</sub> max: 120/110 mA to 110/100/90 mA I <sub>CC3</sub> max: 120/110 mA to 110/100/90 mA I <sub>CC6</sub> max: 120/110 mA to 110/100/90 mA I <sub>CC7</sub> max: 100/90 mA to 100/90/85 mA AC Characteristics t <sub>RRH</sub> min: 0/0 ns to 5/5/5 ns t <sub>RPC</sub> min: 0/0 ns to 5/5/5 ns	Y. Kasama	M. Mishima
3.0	Feb. 24, 1997	AC Characteristics t <sub>RRH</sub> min: 5/5/5 ns to 0/0/0 ns		